



PATENT
Attorney Docket No. 2036/US/2 (1959/US/2)
Express Mail Label No. EV 423 774 530 US

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of:

Romain Desplats et al.

Application No. 10/728,522

Filed: December 5, 2003

For: APPARATUS AND METHOD FOR DETECTING
PHOTON EMISSIONS FROM TRANSISTORS

Confirmation No.: 8276

Art Unit: 2829

Examiner: Not Yet Assigned

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT
Under 37 C.F.R. §§ 1.97(b)(3), 1.97(e)(1), and § 1.98

Sir:

The Information Disclosure Statement submitted herewith is being filed before the mailing date of a first Office action on the merits.

The Examiner is requested to consider the references noted on the enclosed Form PTO-1449 during examination of the above-identified patent application. The references are submitted for the Examiner's consideration and are submitted pursuant to the duty of disclosure under 37 C.F.R. § 1.56. In submitting the references, no representation is made or implied that the references are or are not material to the examination of the application. The Examiner is encouraged to make his or her own determination of materiality. Pursuant to the U.S. Patent and Trademark Office's July 11, 2003 waiver of the requirements of 37 C.F.R. § 1.98(a)(2)(i), only copies of other documents are provided. Copies of the U.S. patent references are not provided.

The references cited and marked with an asterisk (*) on Form PTO-1449 were cited in an International Search Report dated 29 April 2004, in corresponding International Application No. PCT/US03/38616. A copy of the International Search Report is enclosed herewith.

Application No. 10/728,522
Attorney Docket No. 2036/US/2 (1959/US/2)
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The references cited and marked with a double asterisk (**) on Form PTO-1449 were cited in an International Search Report dated 19 April 2004, in related International Application No. PCT/US03/27267. A copy of the International Search Report is enclosed herewith.

Statement Under 37 C.F.R. § 1.97(e)(1)

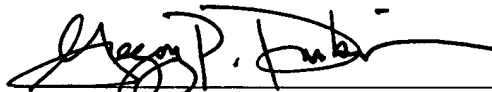
The undersigned hereby certifies that references contained in this information disclosure statement were cited in communications from a foreign patent office in counterpart foreign applications not more than three months prior to the filing of this information disclosure statement.

Accordingly, pursuant to 37 C.F.R. §§ 1.97(b)(3), 1.97(e)(1), no fees are due with respect to this filing. However, should any fees be deemed necessary, such fees may be charged to Deposit Account No. 04-1415.

If the Examiner has any questions, please contact the undersigned attorney.

Dated: June 9, 2004

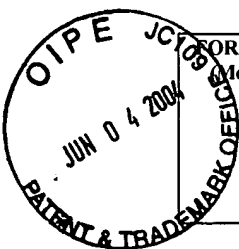
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Enclosures



FORM PTO-1449 U.S. DEPARTMENT OF COMMERCE
(Modified) PATENT AND TRADEMARK OFFICE

**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

(Use several sheets if necessary)

ATTY. DOCKET NO.
2036/US/2 (1959/US/2)

APPLN. NO.
10/728,522

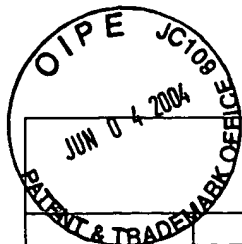
APPLICANT:
Romain Desplats et al.

FILING DATE
December 5, 2003

GROUP
2829

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EXAMINER INITIAL	PATENT NUMBER	ISSUE DATE	PATENTEE	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
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	4,115,694	09/1978	Lange et al.	250	363 S	
	4,242,635	12/1980	Burns	324	158 R	
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	4,555,731	11/1985	Zinchuk	358	209	
	4,591,984	05/1986	Mori	364	414	
	4,680,635	07/1987	Khurana	358	211	
	4,686,371	08/1987	Birch et al.	250	461.1	
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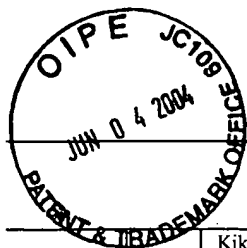
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FOREIGN PATENT OR PUBLISHED FOREIGN PATENT APPLICATION

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						YES	NO

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